

b2
1: a layer (base layer) formed from first III-V compound semiconductor made of high crystal defect density compound semiconductor

2: a pattern formed from material different from first and second III-V compound semiconductors made of, for example, SiO_2

3: a crystal layer (regrown layer) formed from second III-V compound semiconductor wherein the crystal layer has flattened out.

3a): selective growth in microscopic opening

3b): crystal growth beginning to spread over the second III-V compound semiconductor

3c): crystal growth further spreading out over the second III-V compound semiconductor

3d): crystal growth, which has completely grown over the second III-V compound semiconductor.—
